SONY

Diagonal 8mm (Type 1/2) Progressive Scan CCD Image Sensor with Square Pixel for CCIR B/W Video Cameras

Description

The ICX075AL is an interline CCD solid-state image sensor suitable for CCIR black-and-white video cameras. Progressive scan allows all pixels signals to be output independently within approximately 1/50 second. This chip features an electronic shutter with variable charge-storage time which makes it possible to realize full-frame still image without mechanical shutter. Individual pixels in a square matrix make this device suitable for image input and processing applications.

High sensitivity and low dark current are achieved through the adoption of HAD (Hole-Accumulation Diode) sensors.

Features

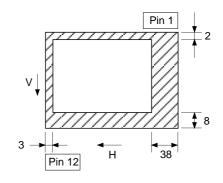
- Progressive scan allows individual readout of the image signals from all pixels.
- High vertical resolution (580TV-lines) still picture without mechanical shutter.
- Square pixel unit cell
- · High resolution, high sensitivity, low dark current
- Continuous variable-speed shutter
- · Low smear
- Excellent antiblooming characteristics
- Reset gate: 5V drive (bias: no adjustment)

Device Structure

Image size:	Diagonal 8mm (Type 1/	2)
• Number of effective pixels:	782 (H) × 582 (V)	approx. 460K pixels
 Total number of pixels: 	823 (H) × 592 (V)	approx. 490K pixels
 Interline CCD image sensor 		
Chip size:	8.10mm (H) × 6.33mm	(V)
Unit cell size:	$8.3\mu m$ (H) $ imes$ $8.3\mu m$ (V)	
Optical black:	Horizontal (H) direction:	Front 3 pixels, rear 38 pixels
	Vertical (V) direction:	Front 8 pixels, rear 2 pixels
 Number of dummy bits: 	Horizontal 19	
	Vertical 5	
 Substrate material: 	Silicon	

22 pin DIP (Cer-DIP)

ICX075AL

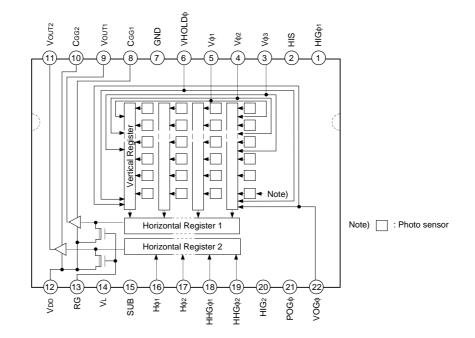


Optical black position (Top View)

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Block Diagram and Pin Configuration

(Top View)



Pin Description

Pin No.	Symbol	Description	Pin No.	Symbol	Description
1	HIGφ1	Test pin *2	12	Vdd	Supply voltage
2	HIS	Test pin *2	13	RG	Reset gate clock
3	Vфз	Vertical register transfer clock	14	VL	Protective transistor bias
4	Vφ2	Vertical register transfer clock	15	SUB	Substrate (overflow drain)
5	Vφ1	Vertical register transfer clock	16	Hφ1	Horizontal register transfer clock
6	VHOLD¢ Vertical register final stage accumulation clock		17	Ηφ2	Horizontal register transfer clock
7	GND	GND	18	HHGφ1	Inter-horizontal register transfer clock
8	CGG1	Output amplifier 1 gate *1 decoupling capacitor	19	HHG _{\$2}	Inter-horizontal register transfer clock
9	Vout1	Signal output 1	20	HIG2	Test pin *2
10	CGG2	Output amplifier 2 gate *1 decoupling capacitor	21	POGø	Test pin *2
11	Vout2	Signal output 2	22	VOGø	Vertical register final stage transfer clock

*1 DC bias is applied within the CCD, so that this pin should be grounded externally through a capacitance of 1µF or more.

*2 Regarding the test pins: apply the same voltage as the supply voltage to HIS, and ground HIGφ₁, HIG₂, and POGφ.

Absolute Maximum Ratings

	Item	Ratings	Unit	Remarks			
Substrate voltage SUB	– GND	-0.3 to +55	V				
Supply voltage	VDD, VOUT1, VOUT2, HIS, CGG1, CGG2 – GND	-0.3 to +18	V				
Supply voltage	VDD, VOUT1, VOUT2, HIS, CGG1, CGG2 – SUB	-55 to +10	V				
	Vφ1, Vφ2, Vφ3, VHOLDφ, VOGφ – GND	-15 to +20	V				
Clock input voltage	Vφ1, Vφ2, Vφ3, VHOLDφ, VOGφ – SUB	to +10	V				
Voltage difference betv	to +15	V	*1				
Voltage difference betv	to +17	V					
Ηφ1, Ηφ2 – VOGφ	Ηφ1, Ηφ2 – VOGφ						
Ηφ1, Ηφ2 – GND		-10 to +15	V				
Ηφ1, Ηφ2 – SUB		-55 to +10	V				
VL – SUB		-65 to +0.3	V				
Vq2, Vq3, Vdd, Vout1, V	Όυτ2, HIS, HIGφ1, HIG2, POGφ – VL	-0.3 to +27.5	V				
RG – GND		-0.3 to +22.5	V				
Vφ1, CGG1, CGG2, Hφ1, H	-0.3 to +17.5	V					
Storage temperature	Storage temperature						
Operating temperature		-10 to +60	°C				

 $^{*1}\,$ +27V (Max.) when clock width < 10µs, clock duty factor < 0.1%.

Bias Conditions

Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
Supply voltage	Vdd	14.55	15.0	15.45	V	
Substrate voltage adjustment range	VSUB	9.0		18.5	V	*1
Substrate voltage adjustment precision		Indicated voltage – 0.1	Indicated voltage	Indicated voltage + 0.1	V	
Protective transistor bias	VL		*2			

DC Characteristics

Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
Supply current	Idd		10		mA	
Input current	lin1			1	μA	*3
Input current	lin2			10	μA	*4

*1 Indications of substrate voltage (VsuB) setting value The setting value of the substrate voltage is indicated on the back of image sensor by a special code. Adjust the substrate voltage (VsuB) to the indicated voltage.

VSUB code - two characters indication

$\mathbf{\Lambda}$	

Integer portion Decimal portion

The integer portion of the code and the actual value correspond to each other as follows.

_____ ↑

Integer portion of code	9	Α	С	d	Е	f	G	h	J	К
Value	9	10	11	12	13	14	15	16	17	18

<Example> "A5" \rightarrow Vsub = 10.5V

- *2 V_L setting is the V_{VL} voltage of the vertical transfer clock waveform, or the same power supply as the V_L power supply for the V driver should be used.
- *3 (1) Current to each pin when 18V is applied to VDD, VOUT1, VOUT2, HIS, RG, CGG1, CGG2, GND and SUB pins, while pins that are not tested are grounded.
 - (2) Current to each pin when 20V is applied sequentially to Vφ1, Vφ2 and Vφ3 pins, while pins that are not tested are grounded. However, 20V is applied to SUB pin.

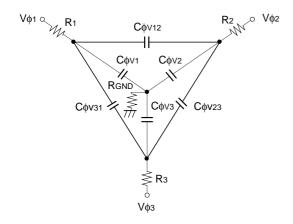
 - (4) Current to VL pin when 25V is applied to Vφ₂, Vφ₃, POGφ, HIGφ₁, HIG₂, V_{DD}, V_{OUT1} and V_{OUT2} pins or when, 15V is applied to Vφ₁, VHOLDφ, VOGφ, C_{GG1}, C_{GG2}, Hφ₁, Hφ₂, HHGφ₁ and HHGφ₂ pins, while VL pin is grounded. However, GND and SUB pins are left open.
 - (5) Current to GND pin when 20V is applied to the RG pin and the GND pin is grounded.
- *4 Current to SUB pin when 55V is applied to SUB pin, while all pins that are not tested are grounded.

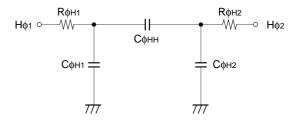
Clock Voltage Conditions

ltem	Symbol	Min.	Тур.	Max.	Unit	Waveform diagram	Remarks
Readout clock voltage	Vvt	14.55	15.0	15.45	V	1	
	Vvh02	-0.05	0	0.05	V	2	Vvh = Vvho2
	VVH1, VVH2, VVH3	-0.2	0	0.05	V	2	
	VVL1, VVL2, VVL3	-8.0	-7.5	-7.0	V	2	$V_{VL} = (V_{VL01} + V_{VL03})/2$
	Vφv	6.8	7.5	8.05	V	2	$V\phi = V + n - V + n (n = 1 \text{ to } 3)$
Vertical transfer clock voltage	Vvl1 – Vvl3			0.1	V	2	
	Vvнн			0.5	V	2	High-level coupling
	Vvhl			0.5	V	2	High-level coupling
	Vvlh			0.5	V	2	Low-level coupling
	VVLL			0.5	V	2	Low-level coupling
Horizontal transfer	Vфн	4.75	5.0	5.25	V	3	
clock voltage	Vhl	-0.05	0	0.05	V	3	
	Vørg	4.5	5.0	5.5	V	4	Input through 0.01µF capacitance
Reset gate clock voltage	Vrglh – Vrgll			0.8	V	4	Low-level coupling
	Vrgh	V _{DD} + 0.4	Vdd + 0.6	Vdd + 0.8	V	4	
Substrate clock voltage	Vфsub	21.5	22.5	23.5	V	5	
Vertical final stage accumulation clock	Vvholdh, Vvogh	-0.05	0	0.05	V	6	
voltage /transfer clock voltage	Vvholdl, Vvogl	-8.0	-7.5	-7.0	V	6	
	Vннд1н, Vннд2н	4.75	5.0	5.25	V	7	
Inter-horizontal register transfer clock voltage	Vhhg1l, Vhhg2l	-8.0	-7.5	-7.0	V	7	
	Vннд1м, Vннд2м	-0.05	0	0.05	V	7	

Clock Equivalent Circuit Constant

Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
	C φv1		820		pF	
Capacitance between vertical transfer clock and GND	C φv2		820		pF	
	Сфvз		820		pF	
	СфV12		3300		pF	
Capacitance between vertical transfer clocks	Сфv23		2200		pF	
	Сф∨з1		2200		pF	
Capacitance between vertical final stage accumulation clock and GND	Covhold		19		pF	
Capacitance between vertical final stage transfer clock and GND	Cφvog		12		pF	
Capacitance between inter-horizontal register transfer	Сфннд1		19		pF	
clock and GND	Сфннд2		19		pF	
Capacitance between horizontal transfer clock and	Сфн1		68		pF	
GND	Сфн2		68		pF	
Capacitance between horizontal transfer clocks	Сфнн		47		pF	
Capacitance between reset gate clock and GND	Cộrg		10		pF	
Capacitance between substrate clock and GND	Сфѕив		400		pF	
Vertical transfer clock series resistor	R1, R2, R3		22		Ω	
Vertical transfer clock ground resistor	Rgnd		15		Ω	
Horizontal transfer clock series resistor	Rфн1		24		Ω	
	Rфн2		24		Ω	



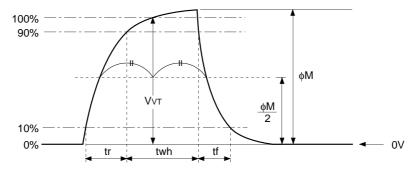


Vertical transfer clock equivalent circuit

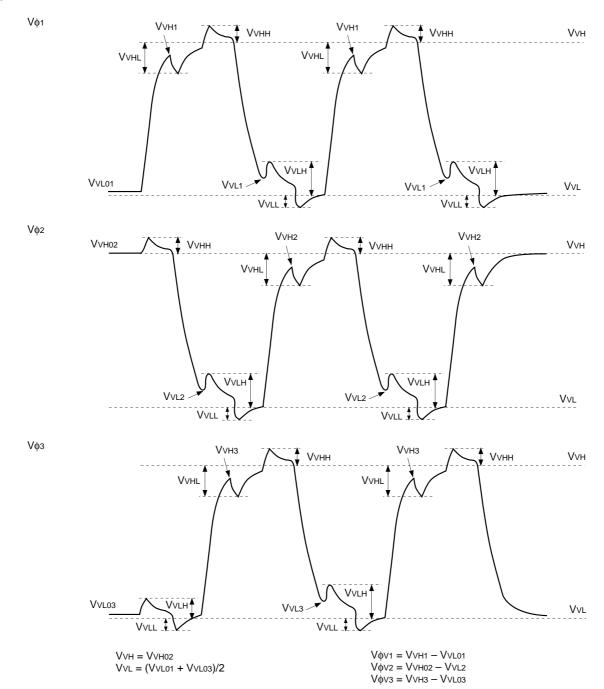


Drive Clock Waveform Conditions

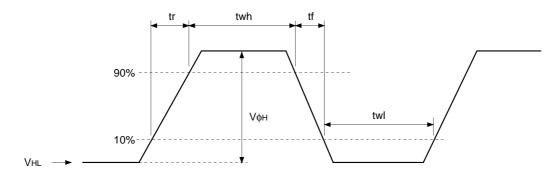
(1) Readout clock waveform



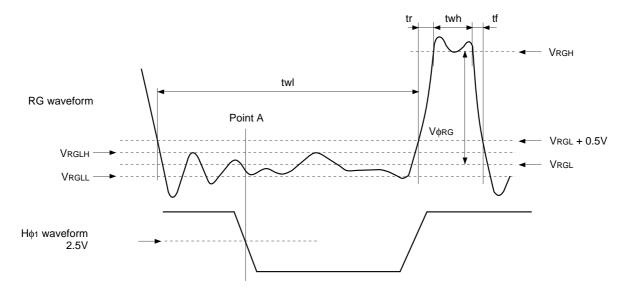
(2) Vertical transfer clock waveform



(3) Horizontal transfer clock waveform



(4) Reset gate clock waveform



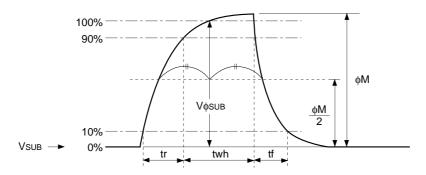
VRGLH is the maximum value and VRGLL is the minimum value of the coupling waveform during the period from Point A in the above diagram until the rising edge of RG. In addition, VRGL is the average value of VRGLH and VRGLL.

VRGL = (VRGLH + VRGLL)/2

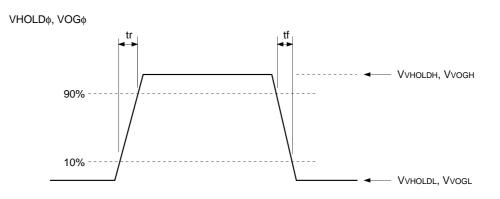
Assuming VRGH is the minimum value during the interval twh, then:

Vørg = Vrgh – Vrgl

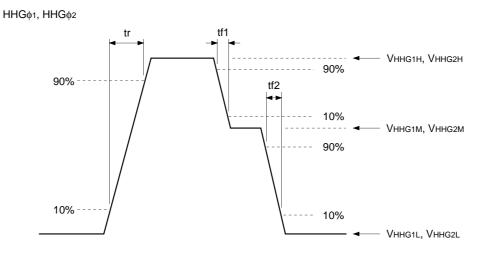
(5) Substrate clock waveform



(6) Vertical final stage accumulation clock waveform · Vertical final stage transfer clock waveform



(7) Inter-horizontal register transfer clock waveform



Clock Switching Characteristics

	ltem Symt			twh			twl			tr		tf,	tf1, t	f2	Unit	Remarks
	nem	Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Unit	Remarks
Re	adout clock	Vт	2.3	2.5						0.4			0.1		μs	During readout
Ve clo	rtical transfer ck	Vφ1, Vφ2, Vφ3										15		400	ns	*1
_÷		Ηφ1	18	23		21	26			10	17.5		10	17.5	20	*2
Horizontal transfer clock	During imaging	Ηφ2	21	26		18	23			10	15		10	15	ns	
Horiz Insfe	During parallel-	Ηφ1								0.01			0.01			
ta –	serial conversion	Ηφ2								0.01			0.01		μs	
Re	set gate clock	φRG	11	14			49			2			2		ns	
Su	bstrate clock	фѕив	1.4	1.6							0.4			0.4	μs	During drain charge
	rtical final stage cumulation/	VHOLDø								20			20		ns	
	nsfer clock	VOGø								20			20		ns	
Inte	er-horizontal	HHGφ1								20			20		ns	
reg	ister transfer clock	HHG _{\$2}								20			20		ns	

*1 When vertical transfer clock driver CXD1268M is used.

ltom	Cumhal		two		ا ا ما ا	Demerica	
ltem	Symbol	Min.	Тур.	Max.	Unit	Remarks	
Horizontal transfer clock	Ηφ1, Ηφ2	20	24		ns	*3	

 *3 The overlap period for twh and twl of horizontal transfer clocks $H\phi_1$ and $H\phi_2$ is two.

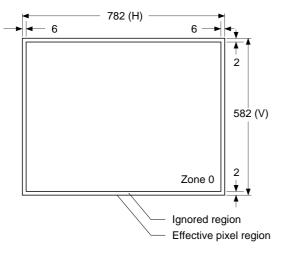
 $(Ta = 25^{\circ}C)$

Image Sensor Characteristics

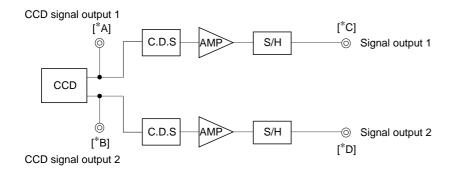
Item	Symbol	Min.	Тур.	Max.	Unit	Measurement method	Remarks
Sensitivity	S	230	300		mV	1	
Saturation signal	Vsat	375			mV	2	Ta = 60°C
Smear	Sm		0.003	0.007	%	3	
Video signal shading	SH			25	%	4	Zone 0
Dark signal	Vdt			2	mV	5	Ta = 60°C
Dark signal shading	ΔVdt			1	mV	6	Ta = 60°C
Lag	Lag			0.5	%	7	
Uniformity between output channels	ΔV			3	%	8	

Note) All the characteristic data of this image sensor was yielded when the sensor was operated in the 1/50s interlaced mode.

Zone Definition of Video Signal Shading



Measurement System



Note) Adjust the amplifier gain so that the gain between [*A] and [*C], and between [*B] and [*D] equals 1.

Readout modes

The output methods for the two readout modes indicated below are now described.

	1/50s interlaced	1/25s non-interlaced
Odd field	Vout1 0 + + + + + + + + + + + + + + + + + +	
Even field	Vout1 0 + + + + + + + + + + + + + + + + + +	Vouti o

1. 1/50s interlaced

In this mode, the signals are output in a 1/50s period using the two output pins (VouT1, VouT2). The signals from two adjacent horizontal lines are simultaneously output from the respective output pins. The lines output from the output pins are changed over with each field. The VouT1 signal after it has passed through the CDS and other external circuits or the signal produced by adding the VouT1 and VouT2 signals accommodate interlaced scanning.

2. 1/25s non-interlaced

In this mode, the signals are output in a 1/25s period using only one output pin (Vout1). Unlike the 1/50s interlaced mode described above, the external circuit can be simplified. The imaging characteristics also differ from those of the other modes.

Image Sensor Characteristics Measurement Method

O Measurement conditions

- 1) In the following measurements, the substrate voltage is set to the value indicated on the device, and the device drive conditions are at the typical values of the bias and clock voltage conditions.
- 2) In the following measurements, spot blemishes are excluded and, unless otherwise specified, the optical black level (OB) is used as the reference for the signal output and the value measured at point [*A] in the measurement system is used.
- 3) In the following measurements, this image sensor is operated in 1/50s interlaced mode.

◎ Definition of standard imaging conditions

1) Standard imaging condition I:

Use a pattern box (luminance 706cd/m², color temperature of 3200K halogen source) as a subject. (Pattern for evaluation is not applicable.) Use a testing standard lens with CM500S (t = 1.00mm) as an IR cut filter and image at F8. The luminous intensity to the sensor receiving surface at this point is defined as the standard sensitivity testing luminous intensity.

2) Standard imaging condition II:

Image a light source (color temperature of 3200K) with a uniformity of brightness within 2% at all angles. Use a testing standard lens with CM500S (t = 1.00mm) as an IR cut filter. The luminous intensity is adjusted to the value indicated in each testing item by the lens diaphragm.

1. Sensitivity

Set to standard imaging condition I. After selecting the electronic shutter mode with a shutter speed of 1/250s, measure the signal output (Vs) at the center of the screen and substitute the value into the following formula.

$$S = Vs \times \frac{250}{50} [mV]$$

2. Saturation signal

Set to standard imaging condition II. After adjusting the luminous intensity to 10 times the intensity with average value of signal output, 120mV, measure the minimum value of the signal output.

3. Smear

Set to standard imaging condition II. With the lens diaphragm at F5.6 to F8, adjust the luminous intensity to 500 times the intensity with average value of signal output, 120mV. When the readout clock is stopped and the charge drain is executed by the electronic shutter at the respective H blankings, measure the maximum value VSm [mV] of the signal output and substitute the value into the following formula.

$$Sm = \frac{VSm}{120} \times \frac{1}{500} \times \frac{1}{10} \times 100 \, [\%] \, (1/10V \text{ method conversion value})$$

4. Video signal shading

Set to standard imaging condition II. With the lens diaphragm at F5.6 to F8, adjust the luminous intensity so that the average value of the signal output is 120mV. Then measure the maximum (Vmax [mV]) and minimum (Vmin [mV]) values of the signal output and substitute the values into the following formula.

 $SH = (Vmax - Vmin)/120 \times 100 [\%]$

5. Dark signal

Measure the average value of the signal output (Vdt [mV]) with the device ambient temperature 60°C and the device in the light-obstructed state, using the horizontal idle transfer level as a reference.

6. Dark signal shading

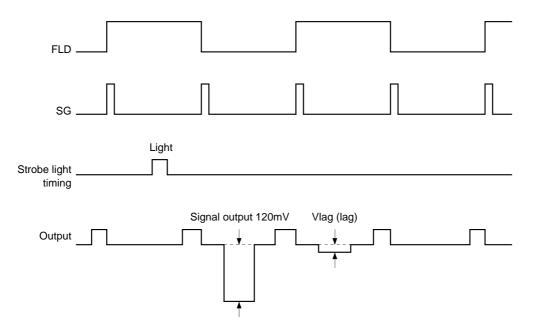
After measuring 5, measure the maximum (Vdmax [mV]) and minimum (Vdmin [mV]) values of the dark signal output and substitute the values into the following formula.

 $\Delta V dt = V dmax - V dmin [mV]$

7. Lag

Adjust the signal output value generated by strobe light to 120mV. After setting the strobe light so that it strobes with the following timing, measure the residual signal (Vlag). Substitute the value into the following formula.

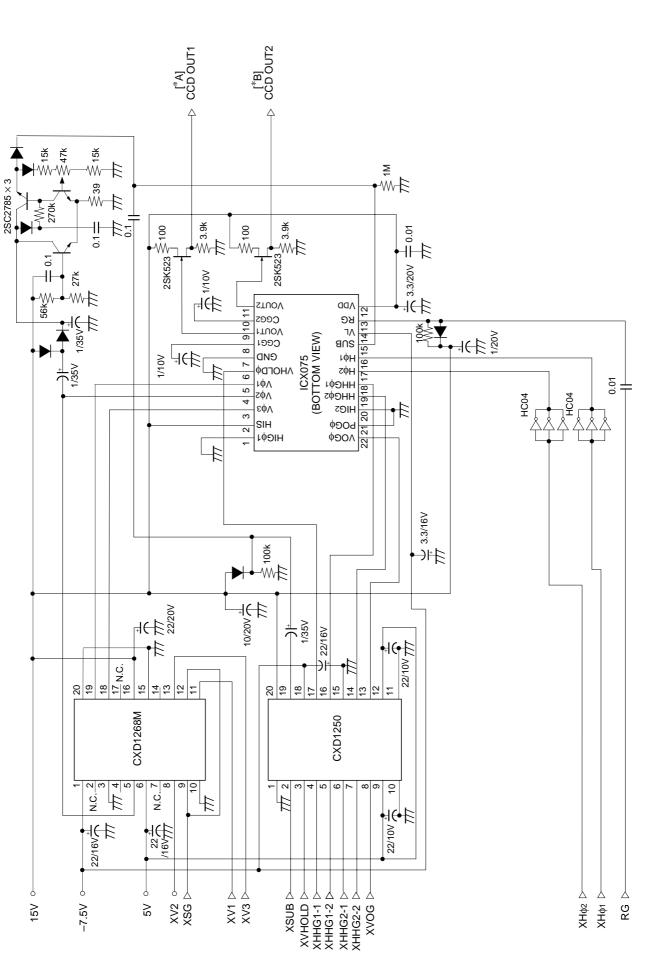
Lag = (Vlag/120) × 100 [%]



8. Uniformity between output channels

Set to standard imaging condition I. Measure the signals at signal output 1 (V1) and at signal output 2 (V2), and substitute the values into the following formula.

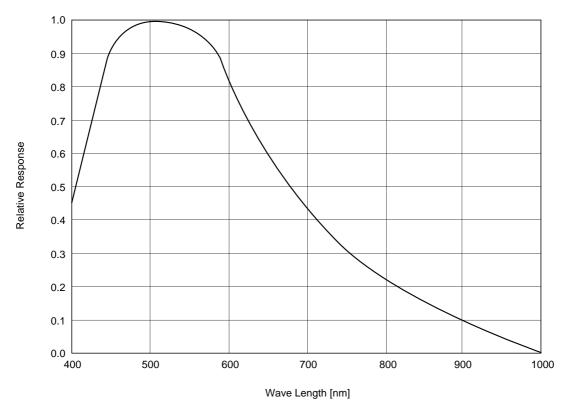
$$\Delta V = \frac{|V2 - V1|}{V1} \times 100 \,[\%]$$

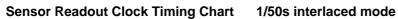


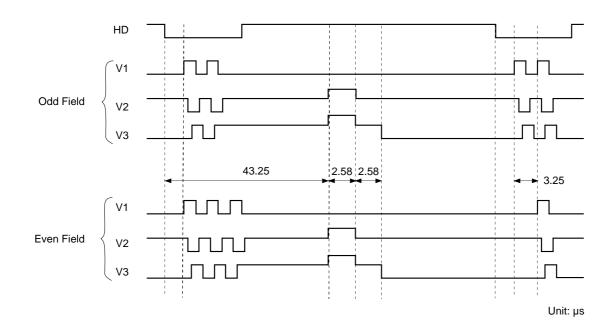
Drive Circuit

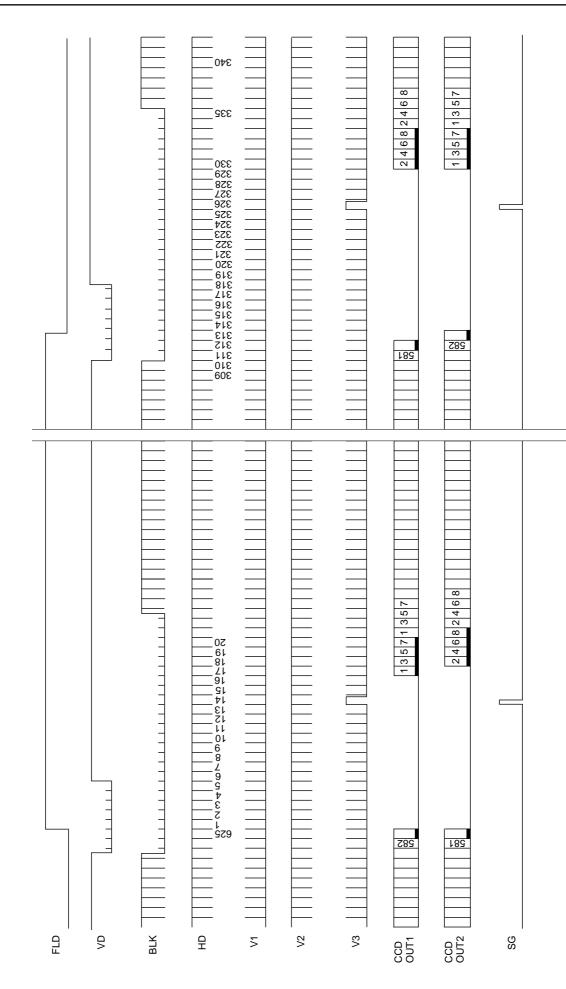
Spectral Sensitivity Characteristics

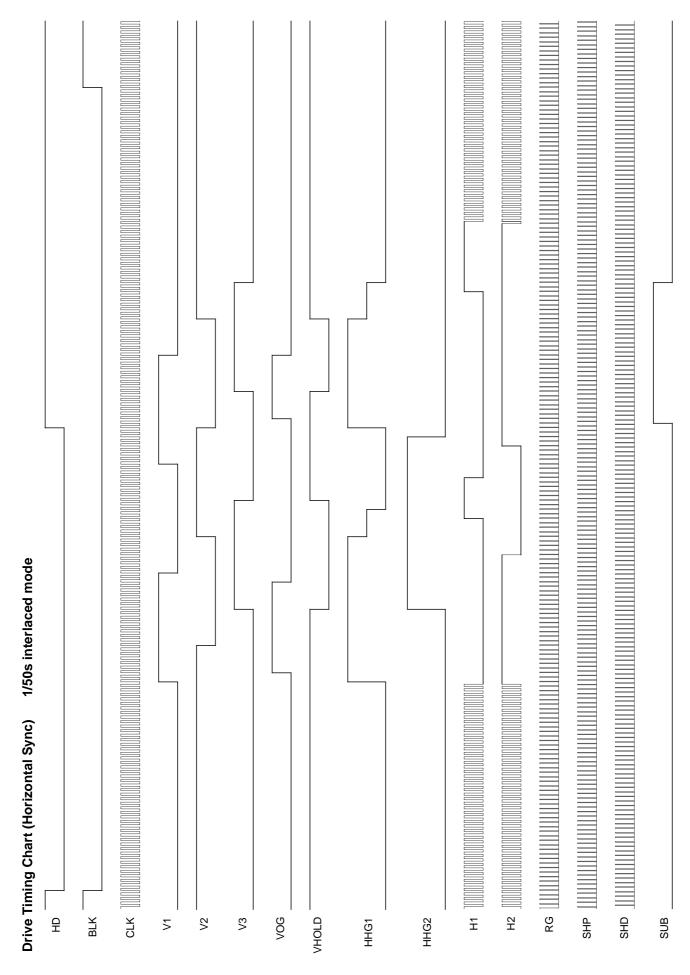
(includes lens characteristics, excludes light source characteristics)











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Notes on Handling

1) Static charge prevention

CCD image sensors are easily damaged by static discharge. Before handling be sure to take the following protective measures.

a) Either handle bare handed or use non-chargeable gloves, clothes or material.

Also use conductive shoes.

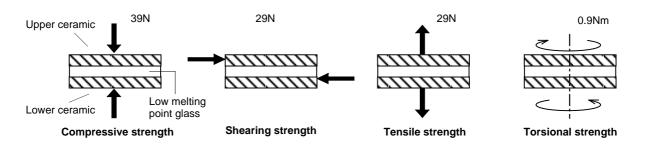
- b) When handling directly use an earth band.
- c) Install a conductive mat on the floor or working table to prevent the generation of static electricity.
- d) Ionized air is recommended for discharge when handling CCD image sensor.
- e) For the shipment of mounted substrates, use boxes treated for the prevention of static charges.

2) Soldering

- a) Make sure the package temperature does not exceed 80°C.
- b) Solder dipping in a mounting furnace causes damage to the glass and other defects. Use a ground 30W soldering iron and solder each pin in less than 2 seconds. For repairs and remount, cool sufficiently.
- c) To dismount an image sensor, do not use a solder suction equipment. When using an electric desoldering tool, use a thermal controller of the zero cross On/Off type and connect it to ground.
- 3) Dust and dirt protection

Image sensors are packed and delivered by taking care of protecting its glass plates from harmful dust and dirt. Clean glass plates with the following operation as required, and use them.

- a) Perform all assembly operations in a clean room (class 1000 or less).
- b) Do not either touch glass plates by hand or have any object come in contact with glass surfaces. Should dirt stick to a glass surface, blow it off with an air blower. (For dirt stuck through static electricity ionized air is recommended.)
- c) Clean with a cotton bud and ethyl alcohol if the grease stained. Be careful not to scratch the glass.
- d) Keep in a case to protect from dust and dirt. To prevent dew condensation, preheat or precool when moving to a room with great temperature differences.
- e) When a protective tape is applied before shipping, just before use remove the tape applied for electrostatic protection. Do not reuse the tape.
- 4) Installing (attaching)
 - a) Remain within the following limits when applying a static load to the package. Do not apply any load more than 0.7mm inside the outer perimeter of the glass portion, and do not apply any load or impact to limited portions. (This may cause cracks in the package.)



b) If a load is applied to the entire surface by a hard component, bending stress may be generated and the package may fracture, etc., depending on the flatness of the ceramic portions. Therefore, for installation, use either an elastic load, such as a spring plate, or an adhesive.

- c) The adhesive may cause the marking on the rear surface to disappear, especially in case the regulated voltage value is indicated on the rear surface. Therefore, the adhesive should not be applied to this area, and indicated values should be transferred to other locations as a precaution.
- d) The upper and lower ceramic are joined by low melting point glass. Therefore, care should be taken not to perform the following actions as this may cause cracks.
 - Applying repeated bending stress to the outer leads.
 - Heating the outer leads for an extended period with a soldering iron.
 - Rapidly cooling or heating the package.
 - Applying any load or impact to a limited portion of the low melting point glass using tweezers or other sharp tools.
 - Prying at the upper or lower ceramic using the low melting point glass as a fulcrum.
 - Note that the same cautions also apply when removing soldered products from boards.
- e) Acrylate anaerobic adhesives are generally used to attach CCD image sensors. In addition, cyanoacrylate instantaneous adhesives are sometimes used jointly with acrylate anaerobic adhesives. (reference)
- 5) Others
 - a) Do not expose to strong light (sun rays) for long periods. For continuous using under cruel condition exceeding the normal using condition, consult our company.
 - b) Exposure to high temperature or humidity will affect the characteristics. Accordingly avoid storage or usage in such conditions.

